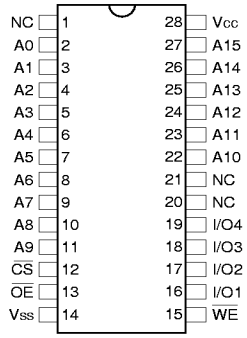
64Kx4 SRAM

*PRELIMINARY**

PIN CONFIGURATION
TOP VIEW



PIN DESCRIPTION

A_{0-15}	Address Inputs
I/O_{0-4}	Data Input/Output
$\overline{CS}$	Chip Select
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
V_{CC}	+5.0V Power
V_{SS}	Ground
NC	Not Connected

PLASTIC PLUS™ FEATURES

- Access Times 15, 17, 20nS
- Standard Commercial Off-The-Shelf (COTS) Memory Devices for Extended Temperature Range
- JEDEC Standard 28 Lead Plastic 0.300" SOJ Package
- Electrical and Speed Characteristics for:
  - Military Temperature (-55°C to +125°C)
  - Industrial Temperature (-40°C to +85°C)
- Burn-in and Temperature Cycling Available
- Organized as 64K x 4
- 5 Volt Power Supply
- Low Power CMOS
- Reliability Test Data Available:
  - High Temperature Operating Life
  - High Temperature Storage
  - Pressure Cooker Test
  - Wet High Temperature Operating Life
  - Thermal Shock
  - Temperature Cycling

* *This data sheet describes a product under development, not fully characterized, and is subject to change without notice.*

PLASTIC *PLUS* SRAM

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature (Mil.)	T_A	-55	+125	°C
Operating Temperature (Ind.)	T_A	-40	+85	°C
Storage Temperature	T_{STG}	-65	+150	°C
Signal Voltage Relative to GND	V_G	-0.5	V_{CC} + 0.5	V
Supply Voltage	V_{CC}	-0.5	7.0	V

TRUTH TABLE

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	Mode	Data I/O	Power
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	X	L	Write	Data In	Active
L	H	H	Out Disable	High Z	Active

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}	4.5	5.5	V
Input High Voltage	V_{IH}	2.2	V_{CC} + 0.5	V
Input Low Voltage	V_{IL}	-0.3	+0.8	V
Operating Temperature (Mil.)	T_A	-55	+125	°C
Operating Temperature (Ind.)	T_A	-40	+85	°C

CAPACITANCE

(T_A = +25°C)

Parameter	Symbol	Condition	Max	Unit
Input capacitance	C_{IN}	V_{IN} = 0V, f = 1.0MHz	6	pF
Output capacitance	C_{OUT}	V_{OUT} = 0V, f = 1.0MHz	8	pF

This parameter is guaranteed by design but not tested.

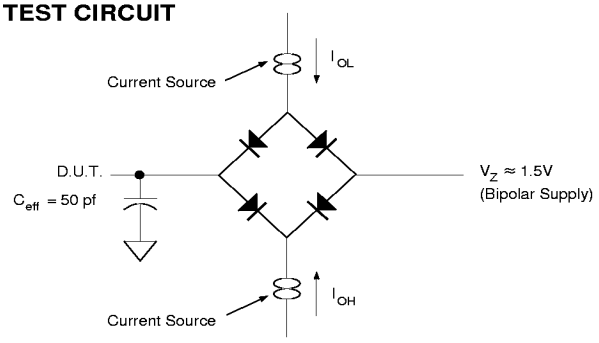
DC CHARACTERISTICS

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter	Symbol	Conditions	Min	Max	Units
Input Leakage Current	I_{LI}	V_{CC} = 5.5, V_{IN} = GND to V_{CC}		10	µA
Output Leakage Current	I_{LO}	$\overline{CS}$ = V_{IH}, $\overline{OE}$ = V_{IH}, V_{OUT} = GND to V_{CC}		10	µA
Operating Supply Current	I_{CC}	$\overline{CS}$ = V_{IL}, $\overline{OE}$ = V_{IH}, f = 5MHz, V_{CC} = 5.5		120	mA
Standby Current	I_{SB}	$\overline{CS}$ = V_{IH}, $\overline{OE}$ = V_{IH}, f = 5MHz, V_{CC} = 5.5		10	mA
Output Low Voltage	V_{OL}	I_{OL} = 8mA, V_{CC} = 4.5		0.4	V
Output High Voltage	V_{OH}	I_{OH} = -4mA, V_{CC} = 4.5	2.4		V

NOTE: DC test conditions: V_{IL} = 0.3V, V_{IH} = V_{CC} -0.3V

AC TEST CIRCUIT



AC TEST CONDITIONS

Parameter	Typ	Unit
Input Pulse Levels	V_{IL} = 0, V_{IH} = 3.0	V
Input Rise and Fall	5	nS
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

NOTES:
V_Z is programmable from -2V to +7V.
I_{OL} & I_{OH} programmable from 0 to 16mA.
Tester Impedance Z_0 = 75 Ω.
V_Z is typically the midpoint of V_{OH} and V_{OL}.
I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.
ATE tester includes jig capacitance.

AC CHARACTERISTICS

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter Read Cycle	Symbol	-15		-17		-20		Units
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	t_{RC}	15		17		20		nS
Address Access Time	t_{AA}		15		17		20	nS
Output Hold from Address Change	t_{OH}	3		3		3		nS
Chip Select Access Time	t_{ACS}		15		17		20	nS
Output Enable to Output Valid	t_{OE}		8		9		10	nS
Chip Select to Output in Low Z	t_{CLZ}[1]	4		4		4		nS
Output Enable to Output in Low Z	t_{OLZ}[1]	0		0		0		nS
Chip Disable to Output in High Z	t_{CHZ}[1]		8		9		10	nS
Output Disable to Output in High Z	t_{OHZ}[1]		8		9		10	nS

1. This parameter is guaranteed by design but not tested.

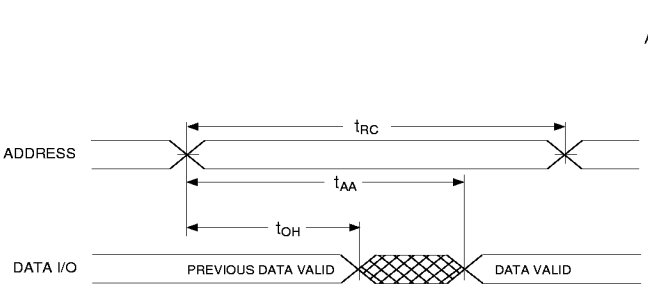
AC CHARACTERISTICS

(V_{CC} = 5.0V, T_A = -55°C to +125°C)

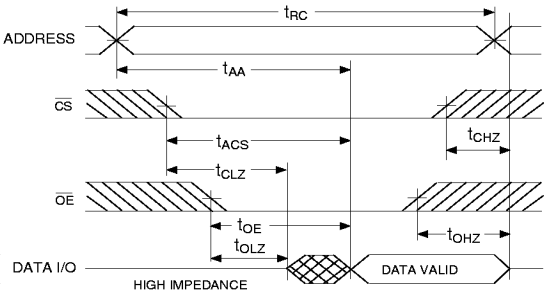
Parameter Write Cycle	Symbol	-15		-17		-20		Units
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	t_{WC}	15		17		20		nS
Chip Select to End of Write	t_{CW}	12		13		14		nS
Address Valid to End of Write	t_{AW}	12		13		14		nS
Data Valid to End of Write	t_{DW}	8		9		10		nS
Write Pulse Width ($\overline{OE}$ = high)	t_{WP}	12		13		14		nS
Address Setup Time	t_{AS}	0		0		0		nS
Address Hold Time	t_{AH}	0		0		0		nS
Output Active from End of Write	t_{OW}[1]	0		0		0		nS
Write Enable to Output in High Z	t_{WHZ}[1]		9		10		11	nS
Data Hold Time	t_{DH}	0		0		0		nS

1. This parameter is guaranteed by design but not tested.

TIMING WAVEFORM - READ CYCLE

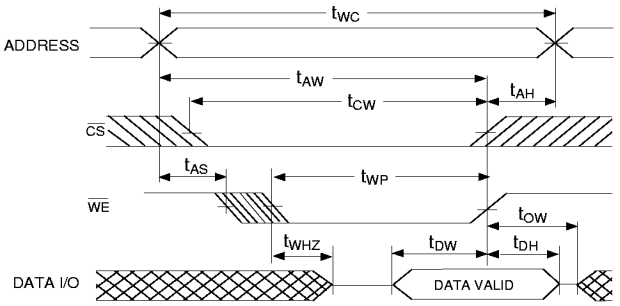


READ CYCLE 1 ($\overline{CS}$ = $\overline{OE}$ = V_{IL}, $\overline{WE}$ = V_{IH})



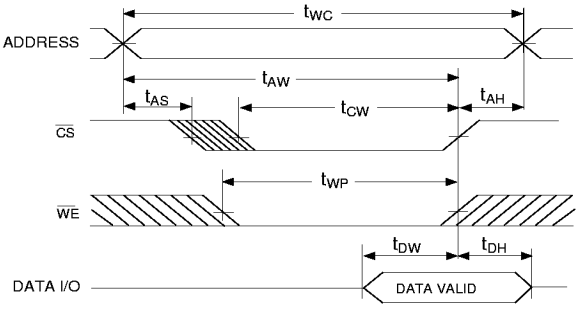
READ CYCLE 2 ($\overline{WE}$ = V_{IH})

WRITE CYCLE - $\overline{WE}$ CONTROLLED



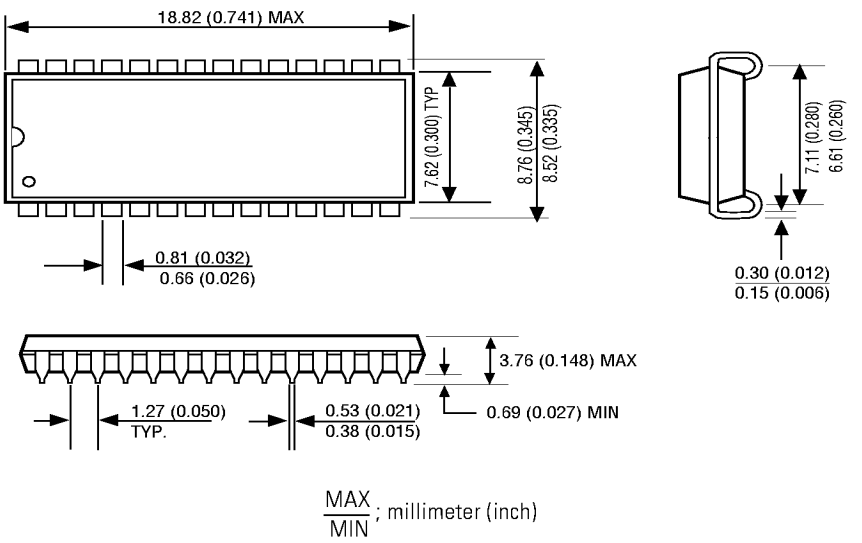
WRITE CYCLE 1, $\overline{WE}$ CONTROLLED

WRITE CYCLE - $\overline{CS}$ CONTROLLED



WRITE CYCLE 2, $\overline{CS}$ CONTROLLED

PACKAGE DIMENSION: 28 LEAD, SOJ



MAX / MIN ; millimeter (inch)

ORDERING INFORMATION

W P S 64K 4 X - XXX SJ X

DEVICE GRADE:
M = Military Temperature -55°C to +125°C
I = Industrial Temperature -40°C to +85°C

PACKAGE:
SJ = 28 Lead SOJ

ACCESS TIME in nS

IMPROVEMENT MARK
B = Burn-in
T = Temperature Cycling
C = Burn-in and Temperature Cycle

ORGANIZATION, 64K x 4

SRAM

PLASTIC PLUS™

WHITE MICROELECTRONICS